

#### 描述 / Descriptions

SOT-23 塑封封装 N 沟道 MOS 场效应管。 N- CHANNEL MOSFET in a SOT-23 Plastic Package.

#### 特征 / Features

芯片采用超高密度圆胞设计技术,R<sub>DS(ON)</sub>导通电阻小,SOT-23 封装。 Super high dense cell design for low R<sub>DS(ON)</sub>,SOT-23 package.

# 3

PIN1: G

PIN 2: S

PIN 3 : D

### 用途 / Applications

电池管理,高速开关,低功率 DC-DC 转换。

Battery management, High speed switch, low power DC to DC converter.

## 印章代码 / Marking

Marking A2SHB
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# 极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数	符号	数值	单位
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Drain Current – Continuous	I <sub>D</sub>	3.0	Α
Pulsed Drain Current	I <sub>DM</sub>	10	Α
Continuous Source Current	I <sub>S</sub>	0.95	Α
Power Dissipation	$P_{D}$	0.9	W
Storage Temperature Range	T <sub>stg</sub>	<b>-</b> 55∼150	$^{\circ}$

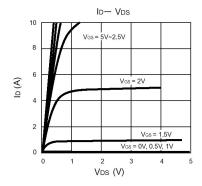


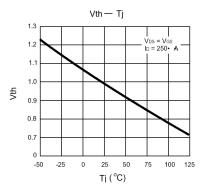
# 电性能参数 / Electrical Characteristics(Ta=25°C)

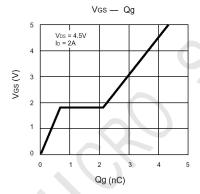
参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain–Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0	I <sub>D</sub> =10μA	20	тур	IVIAA	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> =0	V <sub>DS</sub> =20V			1.0	μΑ
Gate-Body Leakage.	I <sub>GSS</sub>	V <sub>GS</sub> =±8V	V <sub>DS</sub> =0V			±100	nA
Static Drain–Source On–Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> =4.5V	I <sub>D</sub> =3.6A			60	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> =2.5V	I <sub>D</sub> =3.1A		X	115	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V	I <sub>D</sub> =3.6A		8		S
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V	I <sub>D</sub> =1.25A		0.75	1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub>	I <sub>D</sub> =50μA	0.50		1.0	V
State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> =5V	V <sub>GS</sub> =2.5V	4			Α
Turn-On Delay Time	t <sub>d(on)</sub>		-(0)		7		
Turn–On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =10V	I <sub>D</sub> =3.6A		55		20
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ =4.5V $R_{GEN}$ =6 $\Omega$	R <sub>L</sub> =2.8Ω		15		ns
Turn-Off Fall Time	t <sub>f</sub>				10		

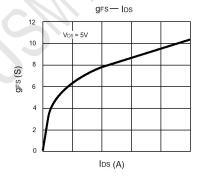


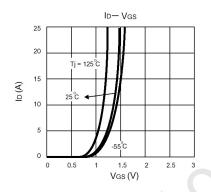
#### 电参数曲线图 / Electrical Characteristic Curve

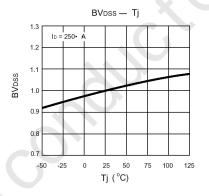


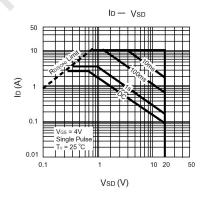


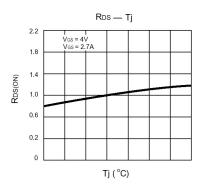










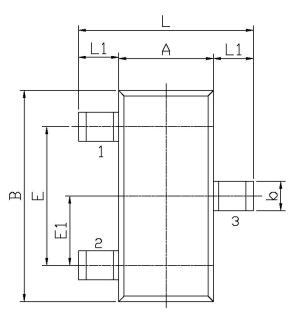


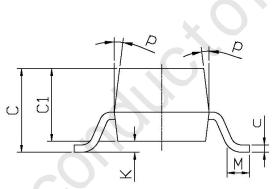


# 外形尺寸图 / Package Dimensions

S0T-23

单位; mm





Symbol	Dimensions In Millmeters		C. mile al	Dimensions In Millmeters		
	Min	Max	Symbol	Min	Max	
L	ณ	2.7	С	1.30Ma×		
L1	0.45	0.65	C1	0.90	1.20	
Α	1.15	1.50	_	0.05	0.20	
В	2.70	3.10	К	0	0.10	
E	1.70	2.10	M	0,20MIN		
E1	0.85	1.05	Р	7°		
b	0.35	0,55				